

STD90GKxxB

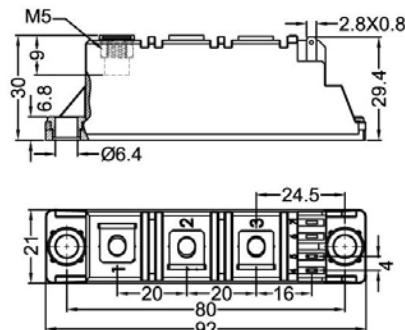
Thyristor-Diode Modules



Type	V _{RSM} V _{DSDM}	V _{RRM} V _{DRM}
	V	V
STD90GK08B	900	800
STD90GK12B	1300	1200
STD90GK14B	1500	1400
STD90GK16B	1700	1600
STD90GK18B	1900	1800



Tolerance: $\pm 0.5\text{mm}$
Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions	Maximum Ratings	Unit	
I _{TRMS} , I _{FRMS}	T _{VJ} =T _{VJM}	180		
I _{TAVM} , I _{FAVM}	T _c =85°C; 180° sine	90	A	
I _{TSM} , I _{FSM}	T _{VJ} =45°C V _R =0	1700 1800	A	
	T _{VJ} =T _{VJM} V _R =0	1540 1640		
$\int i^2 dt$	T _{VJ} =45°C V _R =0	14450 13500	A ² s	
	T _{VJ} =T _{VJM} V _R =0	11850 11300		
(di/dt) _{cr}	T _{VJ} =T _{VJM} f=50Hz, t _p =200us V _D =2/3V _{DRM} I _G =0.45A dI _G /dt=0.45A/us	150 500	A/us	
(dv/dt) _{cr}	T _{VJ} =T _{VJM} ; V _{DR} =2/3V _{DRM} R _{GK} =∞; method 1 (linear voltage rise)	1000	V/us	
P _{GM}	T _{VJ} =T _{VJM} I _T =I _{TAVM}	10 5	W	
P _{GAV}		0.5	W	
V _{RGM}		10	V	
T _{VJ} T _{VJM} T _{stg}		-40...+125 125 -40...+125	°C	
V _{ISOL}	50/60Hz, RMS I _{ISOL} ≤1mA	t=1min t=1s	3000 3600	V~
M _d	Mounting torque (M5) Terminal connection torque (M5)	2.5-4.0/22-35 2.5-4.0/22-35	Nm/lb.in.	
Weight	Typ.	108	g	

Sirectifier®

STD90GKxxB

Thyristor-Diode Modules

Symbol	Test Conditions	Characteristic Values	Unit
I _{RRM} , I _{DRM}	T _{VJ} =T _{VJM} ; V _R =V _{RRM} ; V _D =V _{DRM}	5	mA
V _T , V _F	I _T , I _F =300A; T _{VJ} =25°C	1.74	V
V _{TO}	For power-loss calculations only (T _{VJ} =125°C)	0.85	V
R _T		3.2	mΩ
V _{GT}	V _D =6V; T _{VJ} =25°C T _{VJ} =-40°C	2.5 2.6	V
I _{GT}	V _D =6V; T _{VJ} =25°C T _{VJ} =-40°C	150 200	mA
V _{GD}	T _{VJ} =T _{VJM} ; V _D =2/3V _{DRM}	0.2	V
I _{GD}		10	mA
I _L	T _{VJ} =25°C; t _p =10us; V _D =6V I _G =0.45A; dIg/dt=0.45A/us	450	mA
I _H	T _{VJ} =25°C; V _D =6V; R _{GK} =∞	200	mA
t _{gd}	T _{VJ} =25°C; V _D =1/2V _{DRM} I _G =0.45A; dIg/dt=0.45A/us	2	us
t _q	T _{VJ} =T _{VJM} ; I _T =150A; t _p =200us; -di/dt=10A/us V _R =100V; dv/dt=20V/us; V _D =2/3V _{DRM}	typ. 185	us
Q _s	T _{VJ} =T _{VJM} ; I _T , I _F =50A; -di/dt=6A/us	170	uC
I _{RM}		45	A
R _{thJC}	per thyristor/diode; DC current per module	0.3 0.15	K/W
R _{thJK}	per thyristor/diode; DC current per module	0.5 0.25	K/W
d _s	Creeping distance on surface	12.7	mm
d _A	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * Isolation voltage 3600 V~
- * UL file NO.310749
- * RoHS compliant

APPLICATIONS

- * DC motor control
- * Softstart AC motor controller
- * Light, heat and temperature control

ADVANTAGES

- * Space and weight savings
- * Simple mounting with two screws
- * Improved temperature and power cycling
- * Reduced protection circuits

STD90GKxxB

Thyristor-Diode Modules

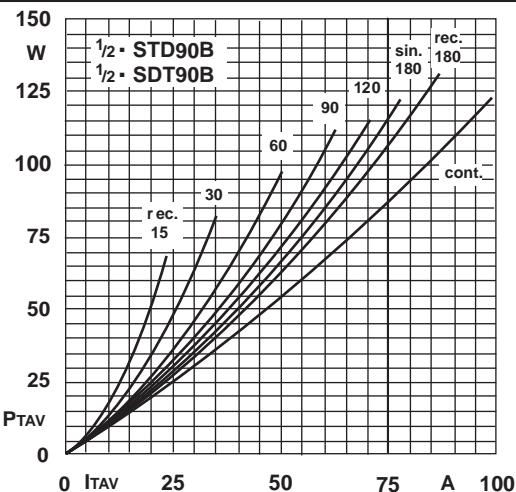


Fig.1L Power dissipation per thyristor vs. on-state current

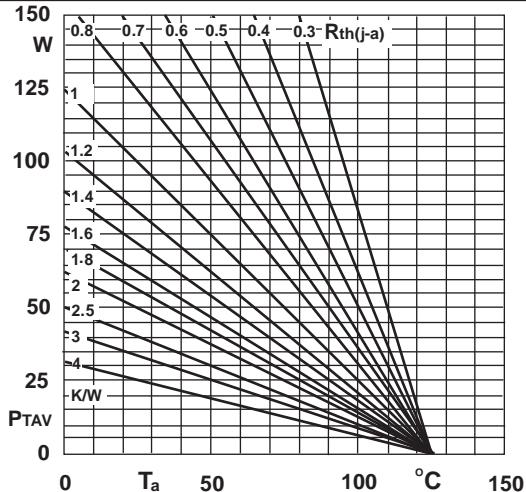


Fig.1R Power dissipation per thyristor vs. ambient temp

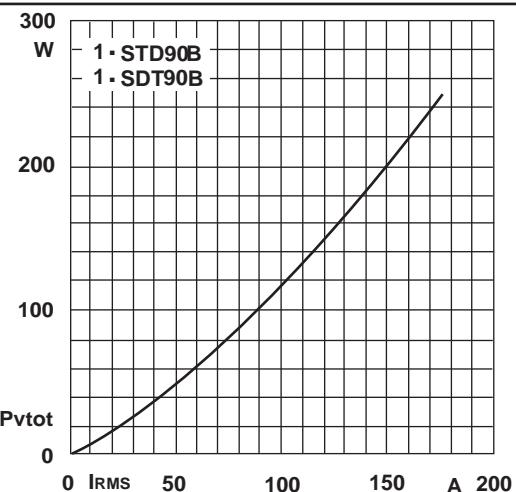


Fig.2L Power dissipation per module vs. rms current

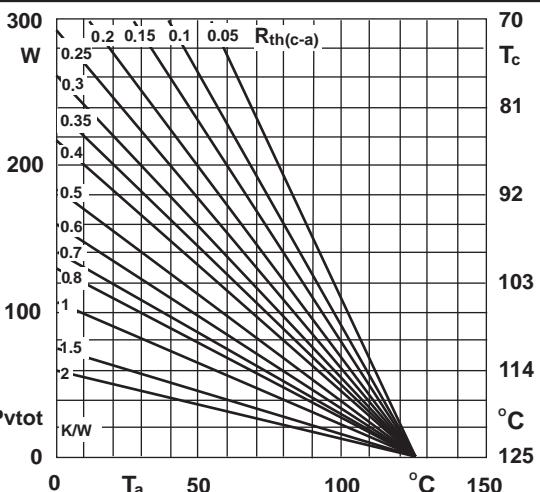


Fig.2R Power dissipation per module vs. case temp

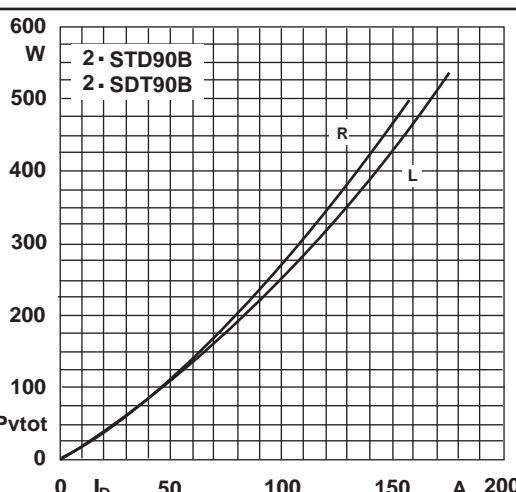


Fig.3L Power dissipation of two modules vs. direct current

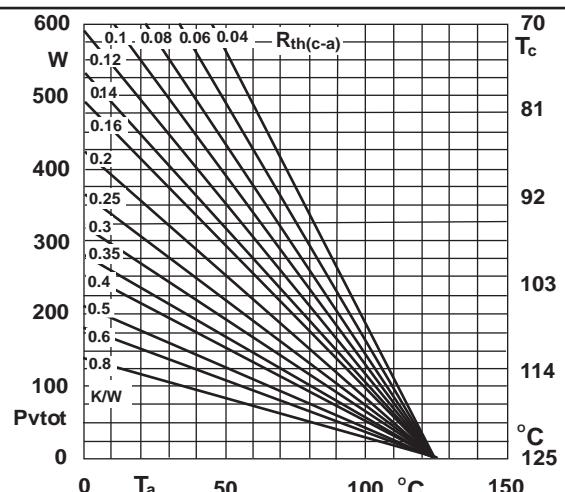


Fig.3R Power dissipation of two modules vs. case temp

STD90GKxxB

Thyristor-Diode Modules

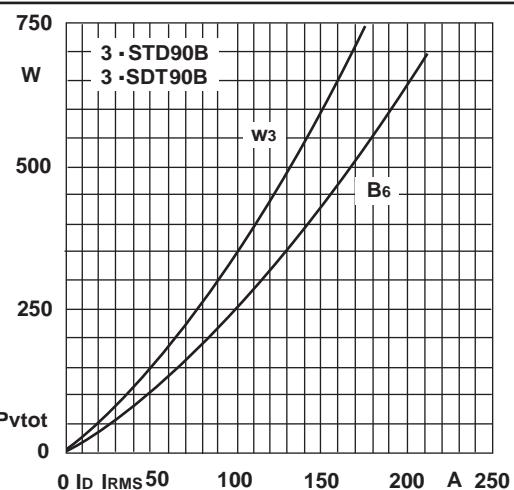


Fig.4L Power dissipation of three modules vs. direct and rms current

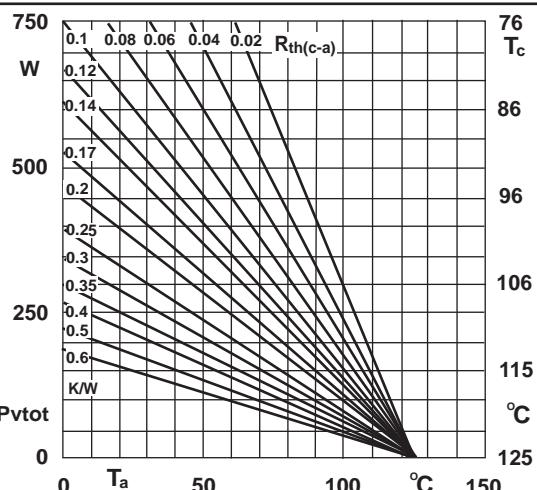


Fig.4R Power dissipation of three modules vs. case temp

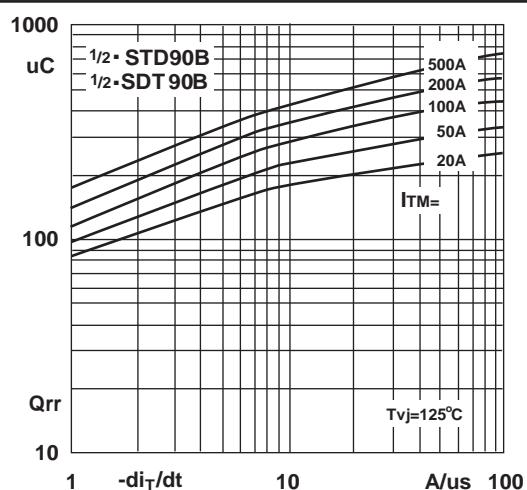


Fig.5 Recovered charge vs. current decrease

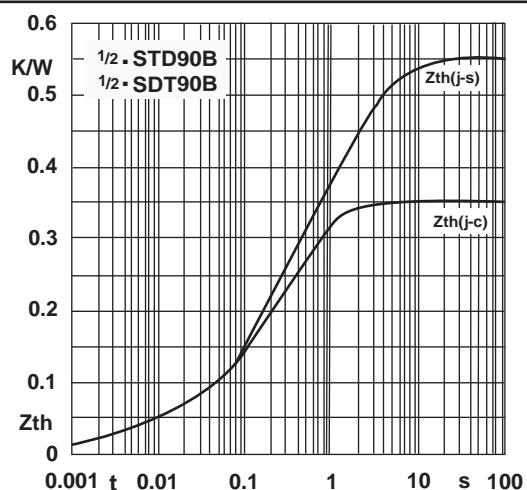


Fig.6 Transient thermal impedance vs. time

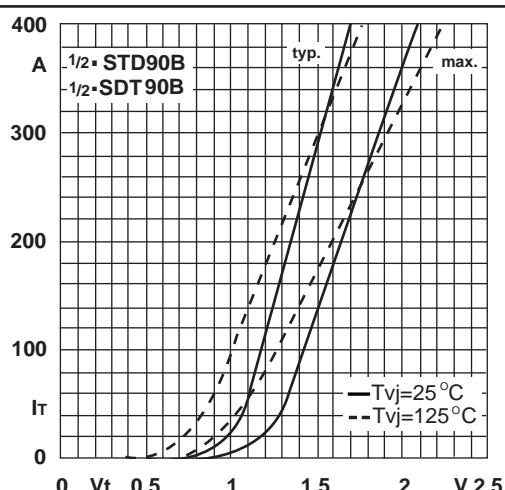


Fig.7 On-state characteristics

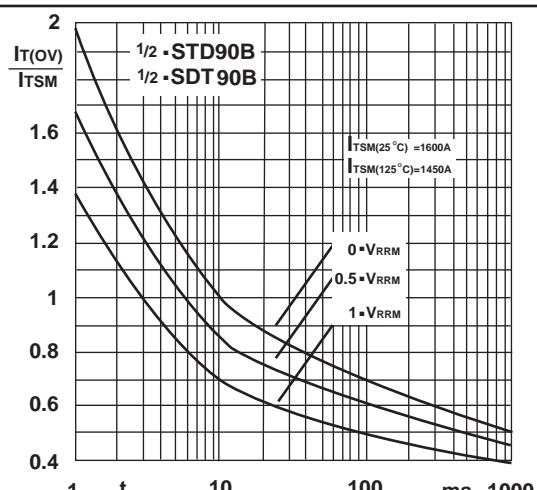


Fig.8 Surge overload current vs. time

Sirectifier®